



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#13/Amdt B  
7/16/03  
C. Pen

In re Patent Application of: )  
Kazuichiroh ITONAGA ) Group Art Unit: 2814  
Serial No. 09/966,741 ) Examiner: Tuan N. Quach  
Filed: October 1, 2001 ) Confirmation No. 3606  
For: SEMICONDUCTOR DEVICE AND ) Date: July 8, 2003  
METHOD FOR MANUFACTURING  
THE SAME

AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

RECEIVED  
JUL 11 2003  
TECHNOLOGY CENTER 2800

Sir:

In response to the Office Action mailed March 13, 2003, please amend the above identified application as follows.

IN THE CLAIMS:

Please amend claims 1, 19, 21, 23 and 24 as follows. Attached hereto is a marked-up copy of the amended claims.

1. (Amended) A method for manufacturing a semiconductor device including a member which is partially silicified, comprising the steps of:
- (a) forming a metal film on a semiconductor layer of a substrate;
  - (b) performing first thermal annealing to cause a silicification reaction between the metal film and the semiconductor layer so as to form a polycrystalline first silicide film that is rich in metal on the semiconductor layer;
  - (c) removing an unreacted portion of the metal film after the step (b);
  - (d) implanting impurity ions into the first silicide film so as to change the first silicide film into an amorphous second silicide film;
  - (e) performing second thermal annealing to change the amorphous second silicide film into a polycrystalline third silicide film, the third silicide film being at least a part of the member.

07/10/2003 CNGUYEN 00000096 09966741

02 FC:1202

144.00 OP